

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX2541FT

LOW-VOLTAGE OCTAL BUS BUFFER WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

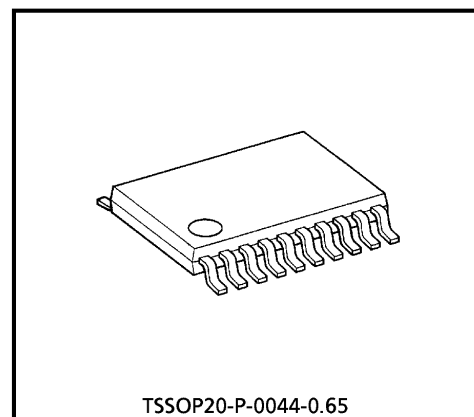
The TC74VCX2541FT is a high performance CMOS OCTAL BUS BUFFER. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This device is a non-inverting 3-state buffer having two active-low output enables. When either $\overline{OE}1$ or $\overline{OE}2$ are high, the terminal outputs are in the high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



TSSOP20-P-0044-0.65

Weight : 0.08 g (Typ.)

FEATURES

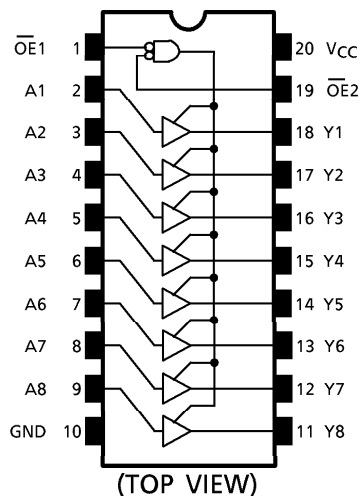
- 26- Ω Series Resistors on Outputs.
- Low Voltage Operation : $V_{CC} = 1.8\sim 3.6$ V
- High Speed Operation : $t_{pd} = 4.4$ ns (max) at $V_{CC} = 3.0\sim 3.6$ V
 $t_{pd} = 5.6$ ns (max) at $V_{CC} = 2.3\sim 2.7$ V
 $t_{pd} = 9.8$ ns (max) at $V_{CC} = 1.8$ V
- 3.6 V Tolerant inputs and output.
- Output Current : $I_{OH}/I_{OL} = \pm 12$ mA (min) at $V_{CC} = 3.0$ V
 $I_{OH}/I_{OL} = \pm 8$ mA (min) at $V_{CC} = 2.3$ V
 $I_{OH}/I_{OL} = \pm 4$ mA (min) at $V_{CC} = 1.8$ V
- Latch-up Performance : ± 300 mA
- ESD Performance : Human Body Model $> \pm 2000$ V
Machine Model $> \pm 200$ V
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 1)

(Note 1) : To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

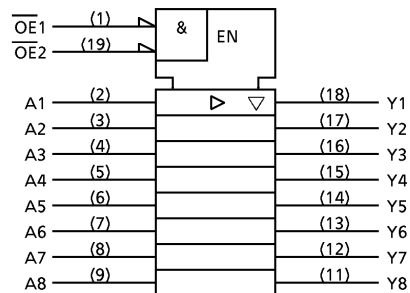
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PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

INPUTS			OUTPUTS
OE1	OE2	An	
H	X	X	Z
X	H	X	Z
L	L	H	H
L	L	L	L

X : Don't Care
 Z : High Impedance

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V _{CC}	-0.5~4.6	V
DC Input Voltage	V _{IN}	-0.5~4.6	V
DC Output Voltage	V _{OUT}	-0.5~4.6 (Note 1)	V
		-0.5~V _{CC} + 0.5 (Note 2)	
Input Diode Current	I _{IJK}	-50	mA
Output Diode Current	I _{OK}	±50 (Note 3)	mA
DC Output Current	I _{OUT}	±50	mA
Power Dissipation	P _D	180	mW
DC V _{CC} /Ground Current	I _{CC} /I _{GND}	±100	mA
Storage Temperature	T _{stg}	-65~150	°C

(Note 1) : Off-State

(Note 2) : High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3) : V_{OUT} < GND, V_{OUT} > V_{CC}

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	V_{OUT}	0~3.6 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	± 12 (Note 7)	mA
		± 8 (Note 8)	
		± 4 (Note 9)	
Operating Temperature	T_{opr}	-40~85	$^{\circ}\text{C}$
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns/V

(Note 4) : Data Retention Only

(Note 5) : Off-State

(Note 6) : High or Low State

(Note 7) : $V_{CC} = 3.0\sim 3.6\text{ V}$ (Note 8) : $V_{CC} = 2.3\sim 2.7\text{ V}$ (Note 9) : $V_{CC} = 1.8\text{ V}$ (Note 10) : $V_{IN} = 0.8\sim 2.0\text{ V}$, $V_{CC} = 3.0\text{ V}$

ELECTRICAL CHARACTERISTICS

DC characteristics ($T_a = -40\sim 85^{\circ}\text{C}$, $2.7\text{ V} < V_{CC} \leq 3.6\text{ V}$)

PARAMETER		SYMBOL	TEST CONDITION	V_{CC} (V)	MIN	MAX	UNIT	
Input Voltage	"H" Level	V_{IH}		2.7~3.6	2.0	—	V	
	"L" Level	V_{IL}		2.7~3.6	—	0.8		
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -100\ \mu\text{A}$	2.7~3.6	$V_{CC} - 0.2$	—	V
				$I_{OH} = -6\text{ mA}$	2.7	2.2	—	
				$I_{OH} = -8\text{ mA}$	3.0	2.4	—	
				$I_{OH} = -12\text{ mA}$	3.0	2.2	—	
	"L" Level	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100\ \mu\text{A}$	2.7~3.6	—	0.2	
				$I_{OL} = 6\text{ mA}$	2.7	—	0.4	
				$I_{OL} = 8\text{ mA}$	3.0	—	0.55	
				$I_{OL} = 12\text{ mA}$	3.0	—	0.8	
Input Leakage Current	I_{IN}	$V_{IN} = 0\sim 3.6\text{ V}$	2.7~3.6	—	± 5.0	μA		
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0\sim 3.6\text{ V}$	2.7~3.6	—	± 10.0	μA		
Power Off Leakage Current	I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6\text{ V}$	0	—	10.0	μA		
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or } \text{GND}$	2.7~3.6	—	20.0	μA		
		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6\text{ V}$	2.7~3.6	—	± 20.0			
Increase In I_{CC} Per Input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6\text{ V}$	2.7~3.6	—	750	μA		

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.3 V ≤ VCC ≤ 2.7 V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN	MAX	UNIT
					2.3~2.7			
Input Voltage	"H" Level	V _{IH}			2.3~2.7	1.6	—	V
	"L" Level	V _{IL}			2.3~2.7	—	0.7	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	2.3	2.0	—	
				I _{OH} = -6 mA	2.3	1.8	—	
				I _{OH} = -8 mA	2.3	1.7	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3~2.7	—	0.2	
				I _{OL} = 6 mA	2.3	—	0.4	
I _{OL} = 8 mA				2.3	—	0.6		
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		2.3~2.7	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.3~2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	—	± 20.0	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 1.8 V ≤ VCC < 2.3 V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN	MAX	UNIT
Input Voltage	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}	—	V
	"L" Level	V _{IL}			1.8~2.3	—	0.2 × V _{CC}	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -4 mA	1.8	1.4	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 4 mA	1.8	—	0.3	
Input Leakage Current		I _{IIN}	V _{IN} = 0~3.6 V		1.8	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6 V		1.8	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	± 20.0	

AC characteristics (Ta = -40~85°C, Input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	MIN	MAX	UNIT
Propagation Delay Time	t _{pLH} t _{pHL}	(Fig.1, 2)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.6	
			3.3 ± 0.3	0.6	4.4	
3-State Output Enable Time	t _{pZL} t _{pZH}	(Fig.1, 3)	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.5	
			3.3 ± 0.3	0.6	5.0	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	(Fig.1, 3)	1.8	1.5	7.7	ns
			2.5 ± 0.2	0.8	4.3	
			3.3 ± 0.3	0.6	3.9	
Output To Output Skew	t _{osLH} t _{osHL}	(Note 11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

(Note 11) : Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics (Ta = 25°C, Input tr = tf = 2.0 ns, CL = 30 pF)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Quiet Output Maximum Dynamic VOL	VOLP	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	0.35	
Quiet Output Minimum Dynamic VOL	VOLV	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	-0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	-0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	-0.35	
Quiet Output Minimum Dynamic VOH	VOHV	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	1.55	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	2.05	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	2.65	

(Note 12) : Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Input Capacitance	C _{IN}		1.8, 2.5, 3.3	6	pF
Output Capacitance	C _{OUT}		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	C _{PD}	f _{IN} = 10 MHz (Note 13)	1.8, 2.5, 3.3	20	pF

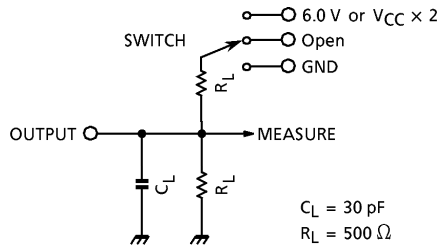
(Note 13) : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$$

TEST CIRCUIT

Fig.1



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V @ $V_{CC} = 3.3 \pm 0.3$ V $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2$ V @ $V_{CC} = 1.8$ V
t_{pHZ}, t_{pZH}	GND

AC WAVEFORM

Fig.2 t_{pLH}, t_{pHL}

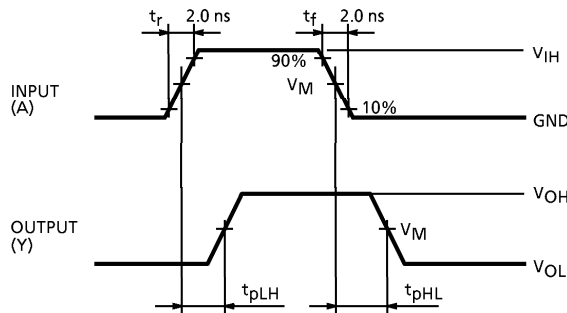
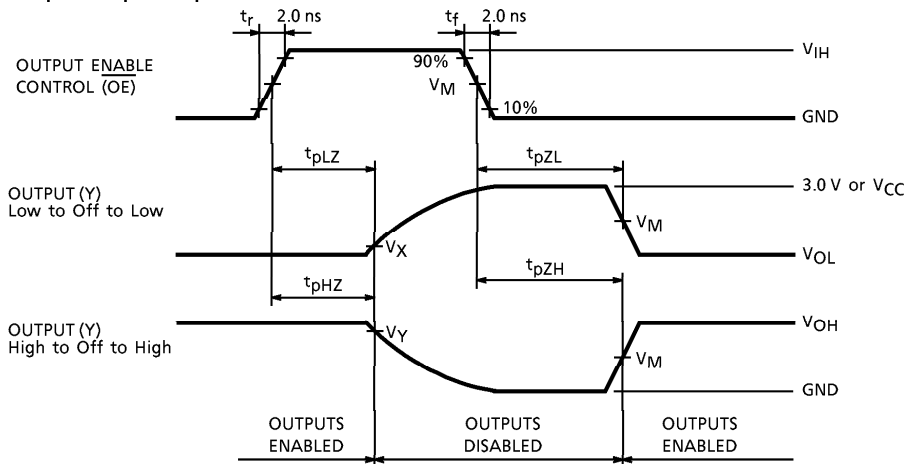


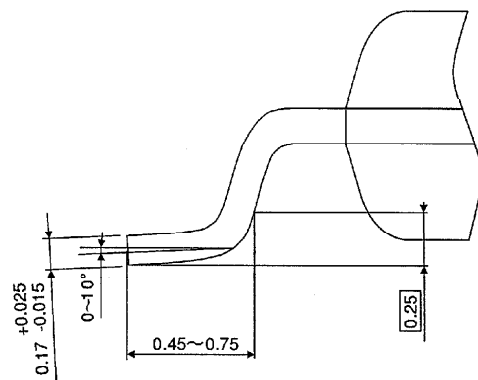
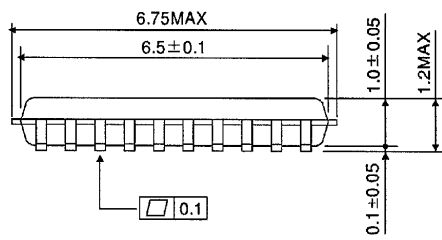
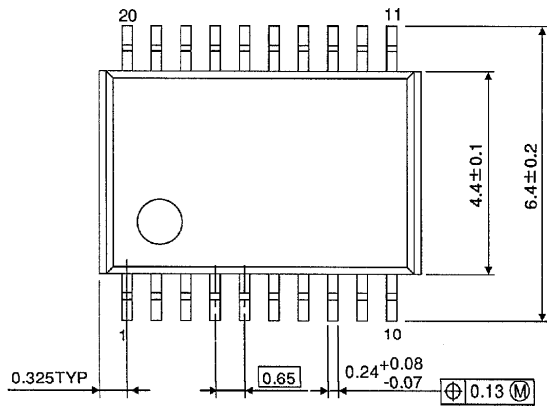
Fig.3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$



SYMBOL	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC} / 2$	$V_{CC} / 2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

OUTLINE DRAWING
TSSOP20-P-0044-0.65

Unit : mm



Weight : 0.08 g (Typ.)